

Silicon PIN Photodiode



21726-1

DESCRIPTION

VBP104FAS and VBP104FASR are high speed and high sensitive PIN photodiodes. It is a surface mount device (SMD) including the chip with a 4.4 mm² sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength 870 nm or 950 nm.

FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 6.4 x 3.9 x 1.2
- Radiant sensitive area (in mm²): 4.4
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 65^\circ$
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmissionsystems, e.g. in combination with TSFFxxxx series IR emitters

PRODUCT SUMMARY

COMPONENT	I _{ra} (μA)	φ (deg)	λ _{0.5} (nm)
VBP104FAS	35	± 65	780 to 1050
VBP104FASR	35	± 65	780 to 1050

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VBP104FAS	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing
VBP104FASR	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	60	V
Power dissipation	T _{amb} ≤ 25 °C	P _V	215	mW
Junction temperature		T _j	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	Acc. reflow solder profile fig. 8	T _{sd}	260	°C
Thermal resistance junction/ambient		R _{thJA}	350	K/W

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50\text{ mA}$	V_F		1	1.3	V
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$, $E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10\text{ V}$, $E = 0$	I_{ro}		2	30	nA
Diode capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		48		pF
	$V_R = 3\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		17	40	pF
Open circuit voltage	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	V_o		350		mV
Temperature coefficient of V_o	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{V_o}		-2.6		mV/K
Short circuit current	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	I_k		32		μA
Temperature coefficient of I_k	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{I_k}		0.1		%/K
Reverse light current	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$, $V_R = 5\text{ V}$	I_{ra}	25	35		μA
Angle of half sensitivity		ϕ		± 65		deg
Wavelength of peak sensitivity		λ_p		950		nm
Range of spectral bandwidth		$\lambda_{0.5}$		780 to 1050		nm
Noise equivalent power	$V_R = 10\text{ V}$, $\lambda = 950\text{ nm}$	NEP		4×10^{-14}		$\text{W}/\sqrt{\text{Hz}}$
Rise time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_r		100		ns
Fall time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_f		100		ns

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

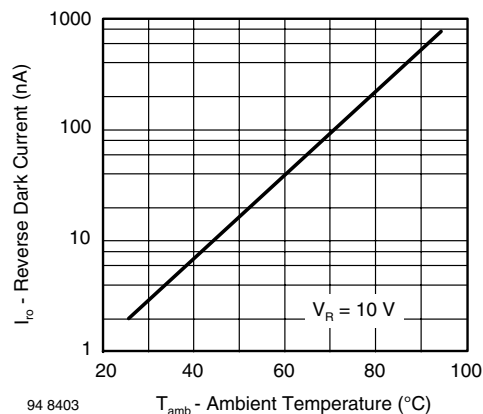


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

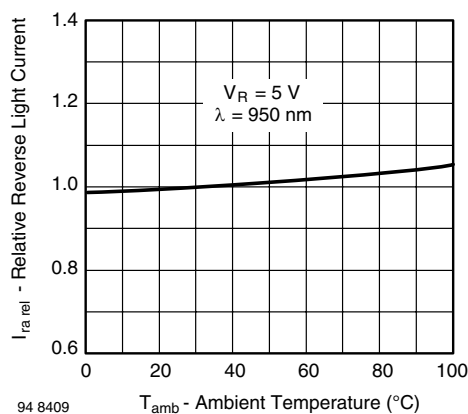


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

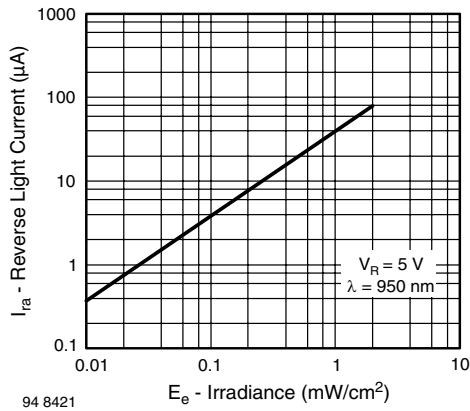


Fig. 3 - Reverse Light Current vs. Irradiance

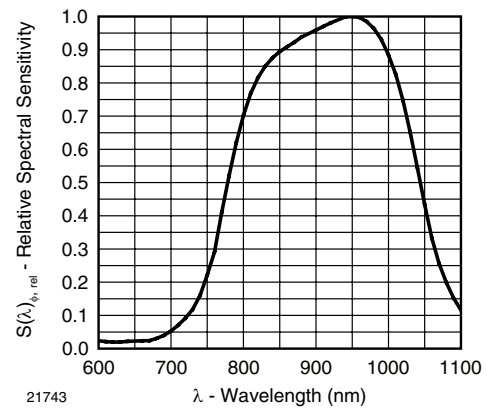


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

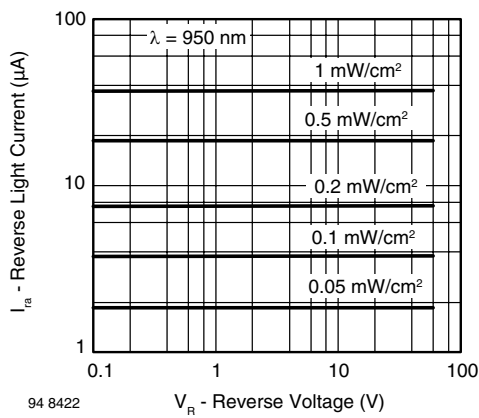


Fig. 4 - Reverse Light Current vs. Reverse Voltage

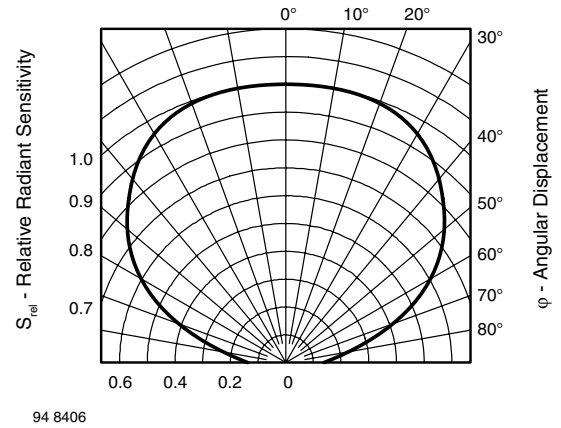


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

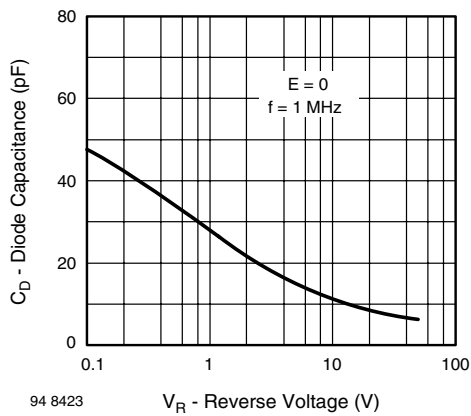


Fig. 5 - Diode Capacitance vs. Reverse Voltage

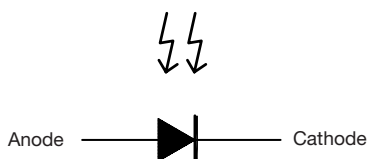
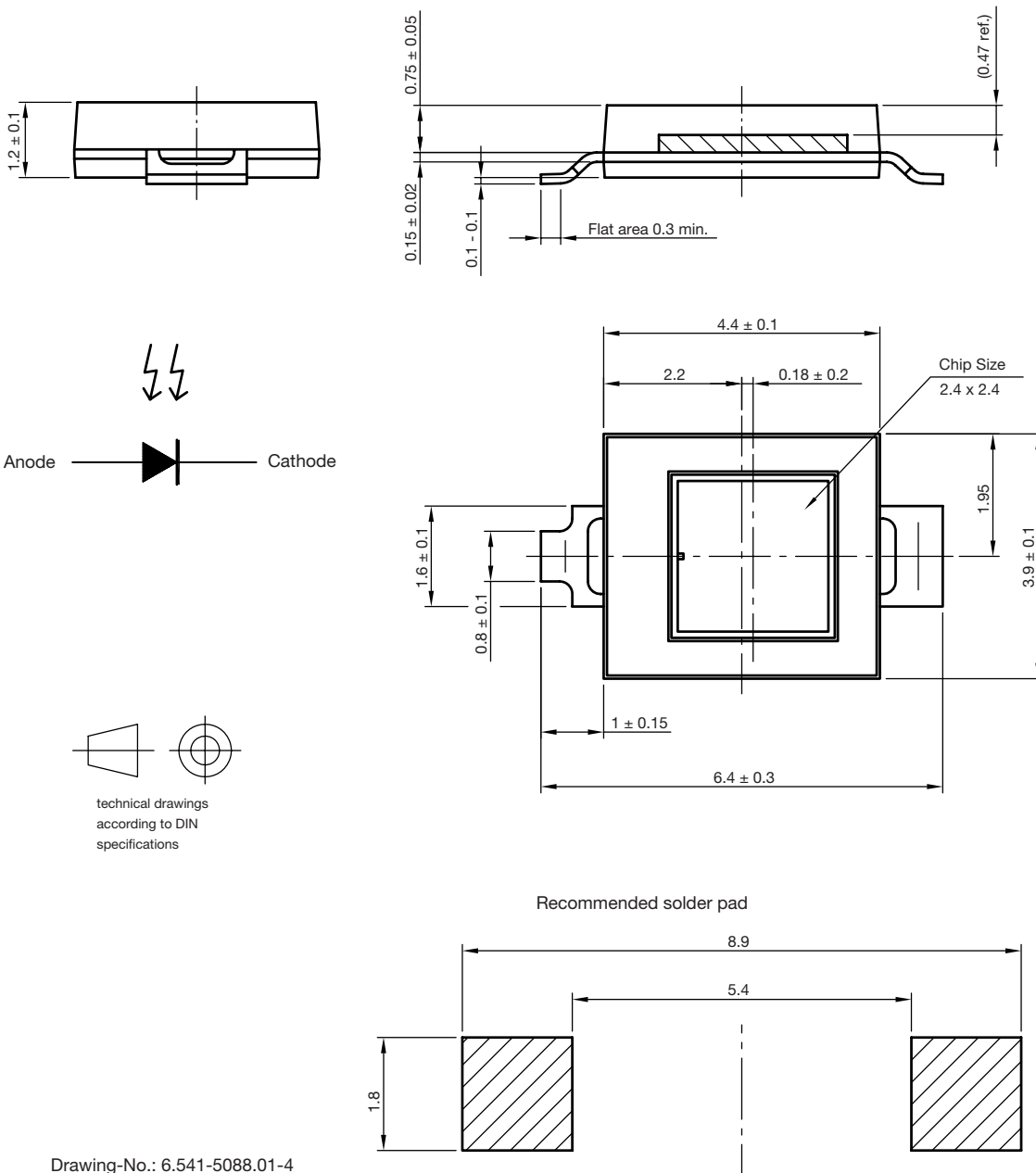
VBP104FAS, VBP104FASR

Vishay Semiconductors

Silicon PIN Photodiode



PACKAGE DIMENSIONS FOR VBP104FAS in millimeters



technical drawings
according to DIN
specifications

Drawing-No.: 6.541-5088.01-4
Issue: 1; 15.04.10
22107

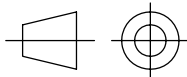
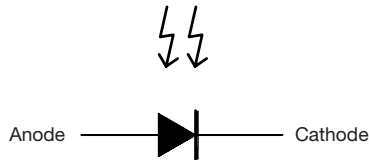
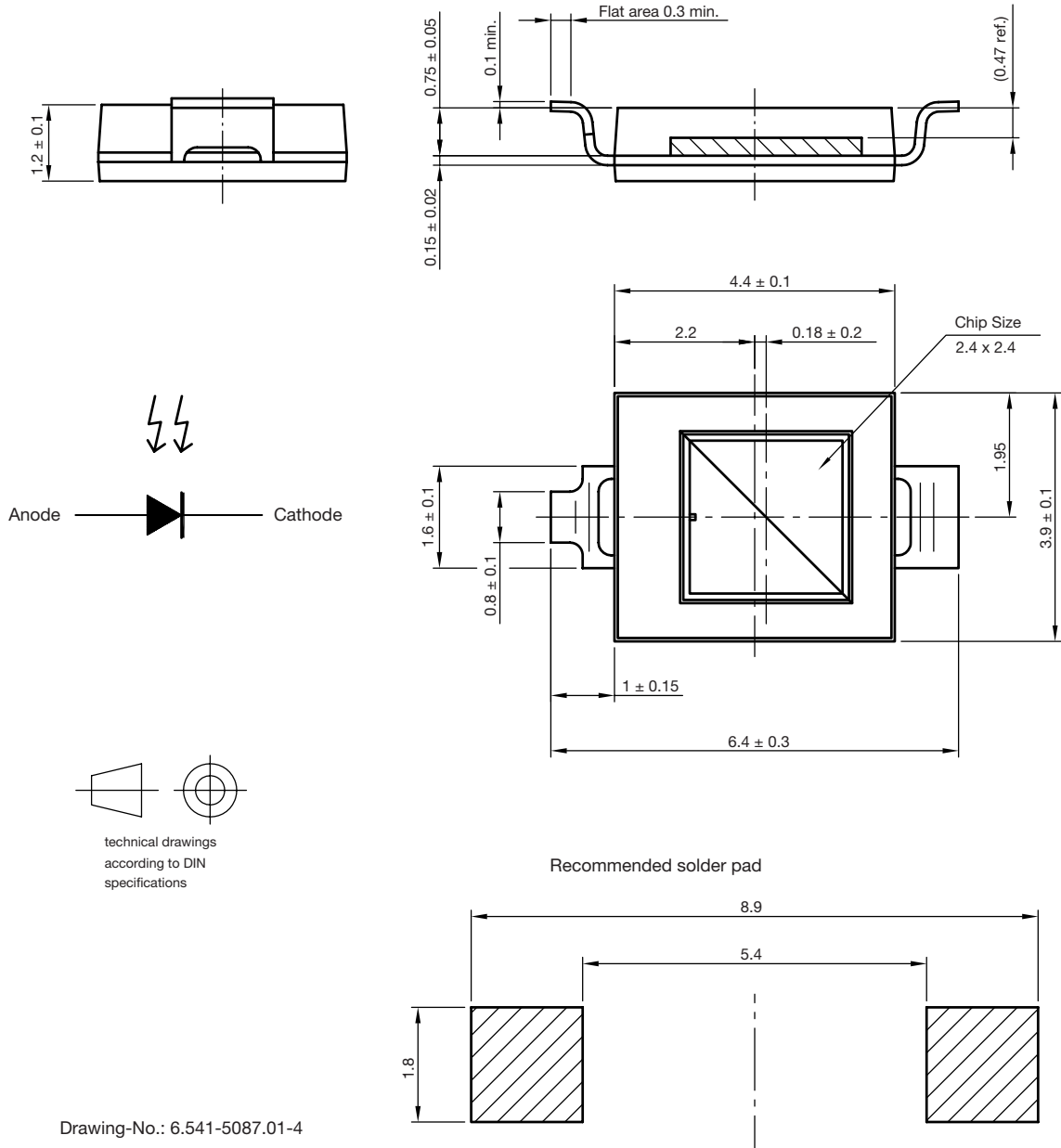


VBP104FAS, VBP104FASR

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Vishay Semiconductors

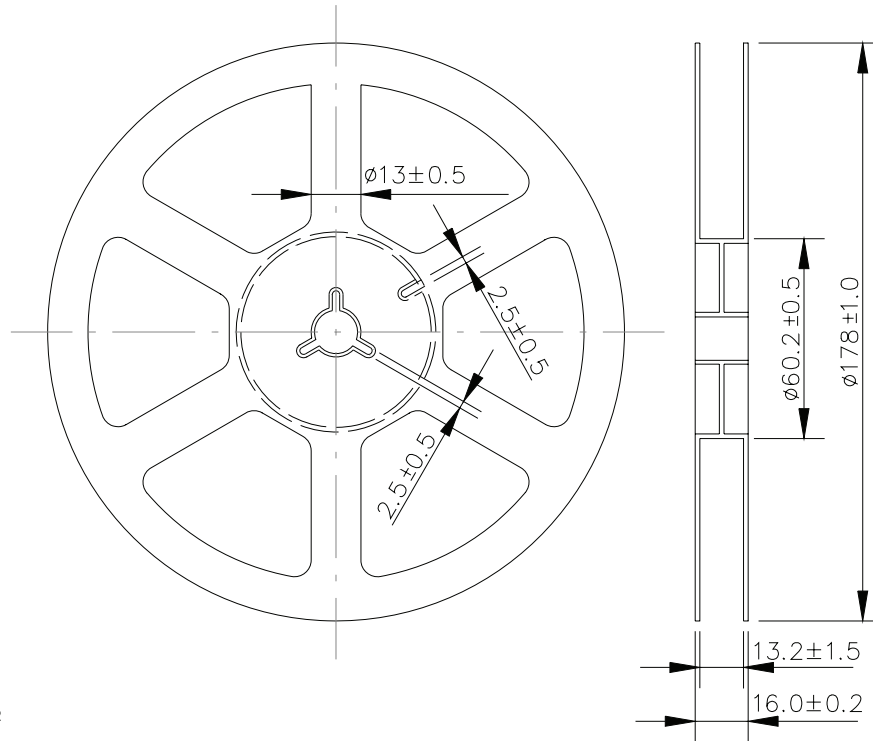
PACKAGE DIMENSIONS FOR VBP104FASR in millimeters



technical drawings according to DIN specifications

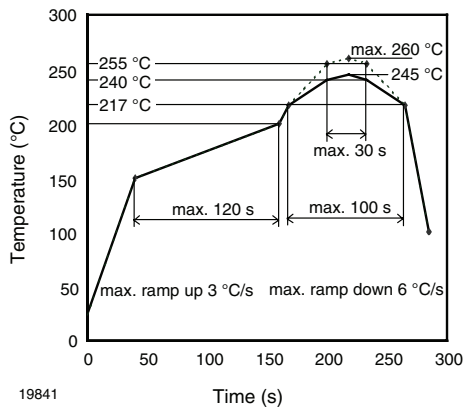
Drawing-No.: 6.541-5087.01-4
Issue: 1; 15.04.10
22106

REEL DIMENSIONS FOR VBP104FAS AND VBP104FASR in millimeters



21732

SOLDER PROFILE



19841

Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

Floor life: 168 h

Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, $\text{RH} < 60\%$

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:

192 h at $40\text{ }^{\circ}\text{C}$ (+ 5 °C), $\text{RH} < 5\%$

or

96 h at $60\text{ }^{\circ}\text{C}$ (+ 5 °C), $\text{RH} < 5\%$.



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